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December 2013

# FPDB60PH60B PFC SPM<sup>®</sup> 3 Series for 2-Phase Bridgeless PFC

## Features

- UL Certified No. E209204 (UL1557)
- 600 V 60 A 2-Phase Bridgeless PFC with Integral Gate Driver and Protection
- Very Low Thermal Resistance Using AIN DBC Substrate
- Built-in NTC Thermistor for Temperature Monitoring
- · Built-in Shunt Resistor for Current Sensing
- Optimized for 20kHz Switching Frequency
- Isolation Rating: 2500 Vrms/min.

## Applications

• 2-Phase Bridgeless PFC Converter

## **Related Source**

 <u>AN-9041 - Bridgeless PFC SPM 3 Series Design</u> <u>Guide</u>

## **General Description**

The FPDB60PH60B is an advanced PFC SPM<sup>®</sup> 3 module providing a fully-featured, high-performance Bridgeless PFC (Power Factor Correction) input power stage for consumer, medical, and industrial applications. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockout, over-current shutdown, thermal monitoring, and fault reporting. These modules also feature high-performance output diodes and shunt resistor for additional space savings and mounting convenience.

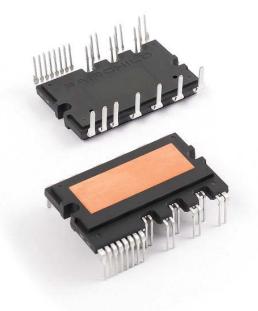


Figure 1. Package Overview

## Package Marking & Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FPDB60PH60B	FPDB60PH60B	SPMHC-027	Rail	10

## Integrated Drive, Protection and System Control Functions

- For IGBTs: gate drive circuit, Over-Current Protection (OCP), control supply circuit Under-Voltage Lock-Out (UVLO) Protection
- Fault signal: corresponding to OC and UV fault
- Built-in thermistor: temperature monitoring
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt-trigger input

## **Pin Configuration**

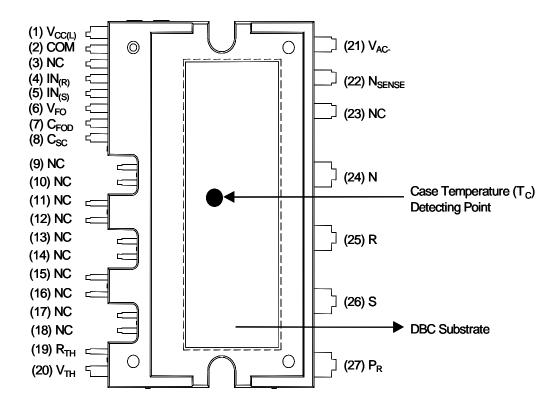
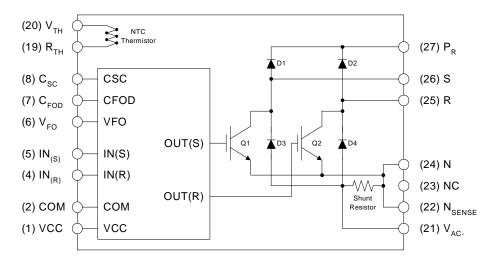


Figure 2. Top View

Pin Number	Pin Name	Pin Description
1	V <sub>CC</sub>	Common Bias Voltage for IC and IGBTs Driving
2	СОМ	Common Supply Ground
4	IN <sub>(R)</sub>	Signal Input for Low-Side R-Phase IGBT
5	IN <sub>(S)</sub>	Signal Input for Low-Side S-Phase IGBT
6	V <sub>FO</sub>	Fault Output
7	C <sub>FOD</sub>	Capacitor for Fault Output Duration Selection
8	C <sub>SC</sub>	Capacitor(Low-Pass Filter) for Over-Current Detection
19	R <sub>(TH)</sub>	Series Resistor for The Use of Thermistor
20	V <sub>(TH)</sub>	Thermistor Bias Voltage
21	V <sub>AC-</sub>	Current Sensing Terminal
22	N <sub>SENSE</sub>	Current Sensing Reference Terminal
24	Ν	Negative Rail of DC-Link
25	R	Output for R-Phase
26	S	Output for S-Phase
27	P <sub>R</sub>	Positive Rail of DC-Link
3, 9~18, 23	NC	No Connection

## Internal Equivalent Circuit



## Figure 3. Internal Block Diagram

#### Notes:

1. Converter is composed of two IGBTs including four diodes and one IC which has gate driving and protection functions.

FPDB60PH60B PFC SPM® 3 Series for 2-Phase Bridgeless PFC

## Absolute Maximum Ratings ( $T_J = 25^{\circ}C$ , unless otherwise specified.) Converter Part

Symbol	Item	Condition	Rating	Unit
V <sub>i</sub>	Supply Voltage	Applied between R - S	264	V <sub>rms</sub>
V <sub>i(Surge)</sub>	Supply Voltage (Surge)	Applied between R - S	500	V
V <sub>PN</sub>	Output Voltage	Applied between P - N	450	V
V <sub>PN(Surge)</sub>	Output Voltage (Surge)	Applied between P - N	500	V
V <sub>CES</sub>	Collector - Emitter Voltage		600	V
$\pm I_{C}$	Each IGBT Collector Current	$T_{C} = 25^{\circ}C$	60	А
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_{C}$ = 25°C, Under 1 ms Pulse Width	90	А
P <sub>C</sub>	Collector Dissipation	T <sub>C</sub> = 25°C per IGBT	178	W
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		600	V
I <sub>FSM</sub>	Peak Forward Surge Current	Single Half Sine-Wave	350	А
P <sub>RSH</sub>	Power Rating of Shunt Resistor	T <sub>C</sub> < 125°C	2	W
Т <sub>Ј</sub>	Operating Junction Temperature	(Note 2)	-40 ~ 150	°C

Notes:

2. The maximum junction temperature rating of the power chips integrated within the PFC SPM<sup>®</sup> product is  $150^{\circ}C(@T_{C} \le 100^{\circ}C)$ .

## **Control Part**

Symbol	Item	Condition	Rating	Unit
V <sub>CC</sub>	Control Supply Voltage	Applied between V <sub>CC</sub> - COM	20	V
V <sub>IN</sub>	Input Signal Voltage	Applied between IN - COM	-0.3 ~ 17.0	V
V <sub>FO</sub>	Fault Output Supply Voltage	Applied between V <sub>FO</sub> - COM	-0.3 ~ V <sub>CC</sub> +0.3	V
I <sub>FO</sub>	Fault Output Current	Sink Current at V <sub>FO</sub> Pin	5	mA
V <sub>SC</sub>	Current Sensing Input Voltage	Applied between C <sub>SC</sub> - COM	-0.3~V <sub>CC</sub> +0.3	V

## **Total System**

Symbol	Item	Condition	Rating	Unit
т <sub>с</sub>	Module Case Operation Temperature		-20 ~ 100	°C
T <sub>STG</sub>	Storage Temperature		-40 ~ 150	°C
V <sub>ISO</sub>	Isolation Voltage	60 Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat-Sink Plate	2500	V <sub>rms</sub>

## **Thermal Resistance**

Symbol	ltem	Condition	Min.	Тур.	Max.	Unit
$R_{\theta(j\text{-}c)Q}$	Junction to Case Thermal Resistance	IGBT	-	-	0.7	°C/W
$R_{\theta(j\text{-}c)HD}$	(Referenced to PKG Center)	High-Side Diode	-	-	1.5	°C/W
$R_{\theta(j\text{-}c)LD}$		Low-Side Diode	-	-	0.85	°C/W

Notes:

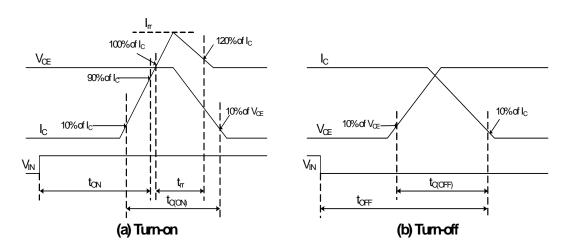
3. For the measurement point of case temperature(T\_C), please refer to Figure 2.

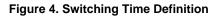
Symbol	Item	Condition	Min.	Тур.	Max.	Unit
V <sub>CE(SAT)</sub>	IGBT Saturation Voltage	$V_{CC} = 15 \text{ V}, \text{ V}_{IN} = 5 \text{ V}, \text{ I}_{C} = 50 \text{ A}$	-	2.0	2.5	V
$V_{FH}$	High-Side Diode Voltage	I <sub>F</sub> = 50 A	-	2.4	2.9	V
V <sub>FL</sub>	Low-Side Diode Voltage	I <sub>F</sub> = 50 A	-	1.2	1.6	V
t <sub>ON</sub>	Switching Times	$V_{PN} = 400 \text{ V}, V_{CC} = 15 \text{ V}, I_{C} = 60 \text{ A}$	-	560	-	ns
t <sub>C(ON)</sub>	-	$V_{IN} = 0 V \leftrightarrow 5 V$ , Inductive Load (Note 4)	-	270	-	ns
t <sub>OFF</sub>			-	520	-	ns
t <sub>C(OFF)</sub>			-	110	-	ns
t <sub>rr</sub>			-	44	-	ns
I <sub>rr</sub>			-	6.5	-	А
R <sub>SENSE</sub>	Current-Sensing Resistor		1.8	2.0	2.2	mΩ
I <sub>CES</sub>	Collector - Emitter Leakage Current	V <sub>CE</sub> = V <sub>CES</sub>	-	-	250	μΑ

# **Electrical Characteristics** ( $T_J = 25^{\circ}C$ , unless otherwise specified.)

Notes: 4. t<sub>ON</sub>

ton and tore include the propagation delay of the internal drive IC. t<sub>C(ON)</sub> and t<sub>C(OFF)</sub> are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

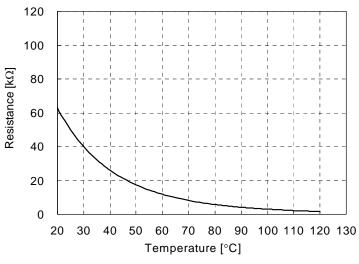


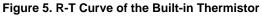


Symbol	Item	Condition	Min.	Тур.	Max.	Unit
IQCCL	Quiescent V <sub>CC</sub> Supply Current	V <sub>CC</sub> = 15 V, IN = 0 V V <sub>CC</sub> - COM	-	-	26	mA
V <sub>FOH</sub>	Fault Output Voltage	$V_{SC}$ = 0 V, $V_{FO}$ Circuit: 4.7 k $\Omega$ to 5 V Pull-up	4.5	-	-	V
V <sub>FOL</sub>		$V_{SC}$ = 1 V, $V_{FO}$ Circuit: 4.7 k $\Omega$ to 5 V Pull-up	-	-	0.8	V
V <sub>SC(ref)</sub>	Over-Current Trip Level	V <sub>CC</sub> = 15 V	0.45	0.50	0.55	V
UV <sub>CCD</sub>	Supply Circuit Under-Voltage	Detection Level	10.7	11.9	13.0	V
UV <sub>CCR</sub>	Protection	Reset Level	11.2	12.4	13.2	V
t <sub>FOD</sub>	Fault-Out Pulse Width	C <sub>FOD</sub> = 33 nF (Note 5)	1.4	1.8	2.0	ms
V <sub>IN(ON)</sub>	ON Threshold Voltage	Applied between IN - COM	3.0	-	-	V
V <sub>IN(OFF)</sub>	OFF Threshold Voltage		-	-	0.8	V
R <sub>TH</sub>	Resistance of Thermistor	at $T_{C} = 25^{\circ}C$ (See Figure 5)	-	50	-	kΩ
		at T <sub>C</sub> = 80°C (See Figure 5)	-	5.76	-	kΩ

**Notes:** 5. The fault-out pulse width  $t_{FOD}$  depends on the capacitance value of  $C_{FOD}$  according to the following approximate equation:  $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$ 

### R-T Graph





## **Recommended Operating conditions**

Symbol	Item	Condition	Min.	Тур.	Max.	Unit
VI	Input Supply Voltage	Applied between R - S	180	-	264	V <sub>rms</sub>
V <sub>PN</sub>	Output Voltage	Applied between P - N	-	280	400	V
V <sub>CC</sub>	Control Supply Voltage	Applied between V <sub>CC</sub> - COM	13.5	15	16.5	V
dV <sub>CC</sub> /dt	Control Supply Variation	Applied between IN - COM	-1	-	1	V/µs
f <sub>PWM</sub>	PWM Input Signal	$T_C \leq 100^\circ C,  T_J \leq 125^\circ C,  per  IGBT$	-	20	-	kHz

Mechanical C	haracteristics and	Ratings				
ltem		Condition	Min.	Тур.	Max.	Units
Mounting Torque	Mounting Screw: M3	Recommended 0.62 N•m	0.51	0.62	0.72	N∙m
Device Flatness	See Figure 6		0	-	+120	μm
Weight			-	15.00	-	g

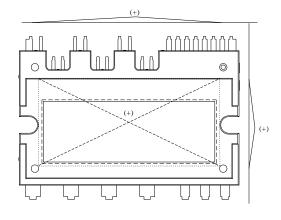
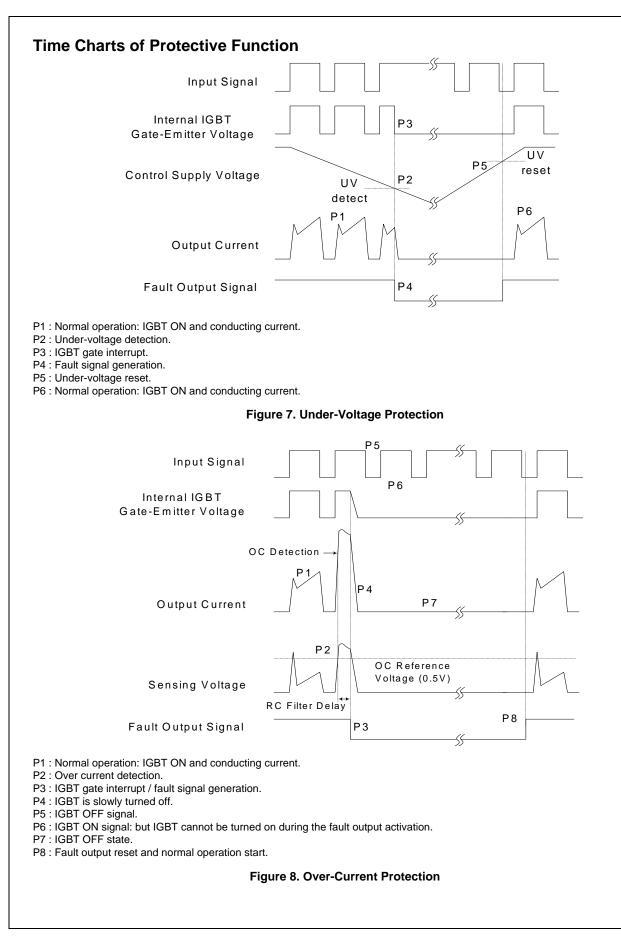
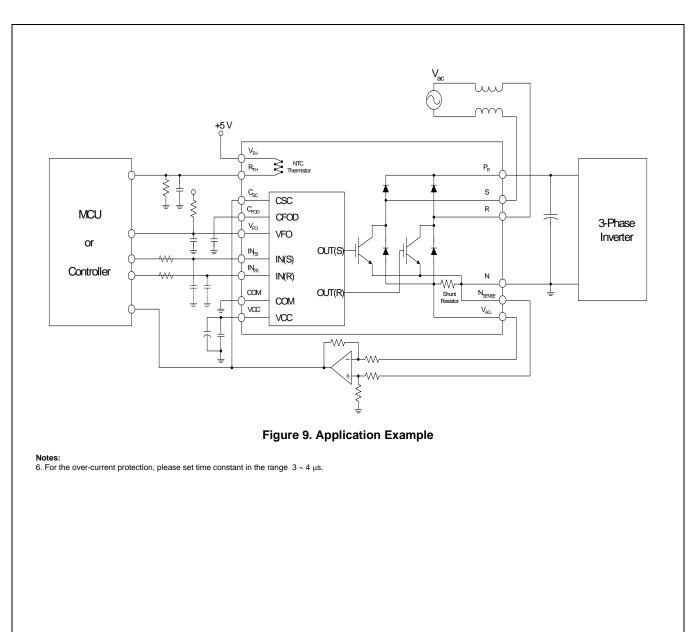
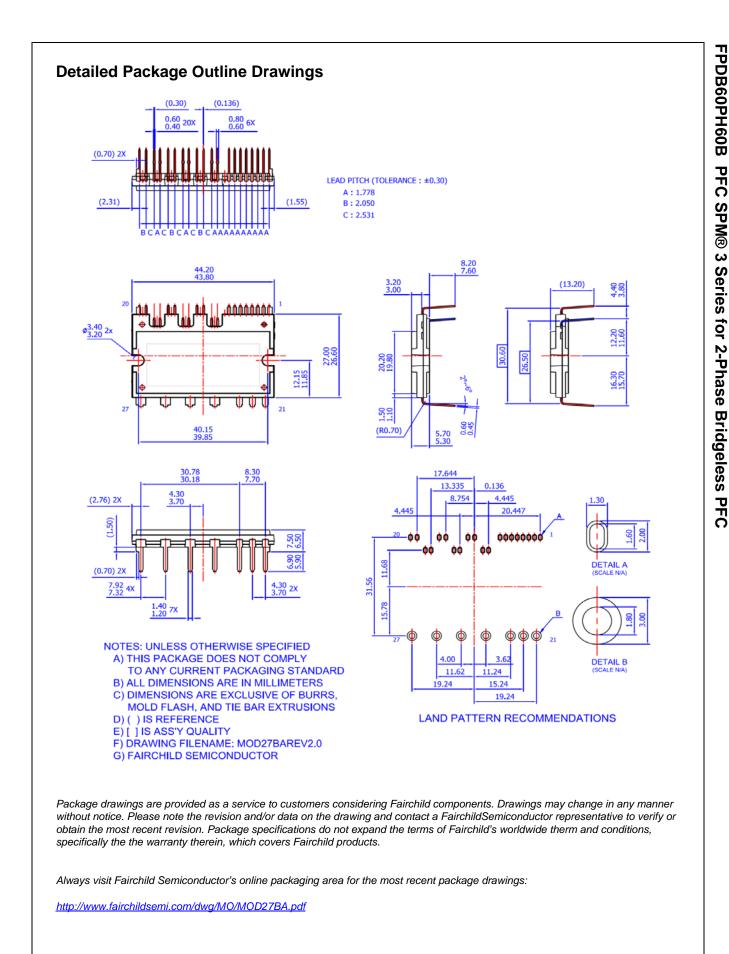


Figure 6. Flatness Measurement Position









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